ABSTRACT OF THE DISCLOSURE

A heterojunction type compound semiconductor field effect transistor includes a channel layer, a first electron supply layer, an electric field strength reducing layer, a first contact layer, a recess stopper layer, and a second contact layer sequentially stacked on a compound semiconductor substrate. This transistor has a double recess structure. The first contact layer is composed of GaAs or InGaAs doped with n type impurities with a high electron mobility. The electric field strength reducing layer is composed of intrinsic InGaP.